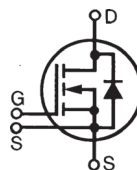


PolarHV™ HiPerFET IXFN 80N50P Power MOSFET

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode

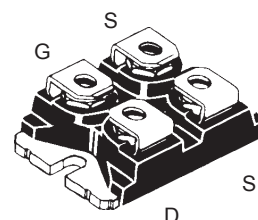
$$\begin{aligned} V_{DSS} &= 500 \text{ V} \\ I_{D25} &= 66 \text{ A} \\ R_{DS(on)} &\leq 65 \text{ m}\Omega \\ t_{rr} &\leq 200 \text{ ns} \end{aligned}$$



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	500	V
V_{GS}	Transient	± 40	V
V_{GSM}	Continuous	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	66	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	200	A
I_{AR}	$T_C = 25^\circ\text{C}$	80	A
E_{AR}	$T_C = 25^\circ\text{C}$	80	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	3.0	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2 \Omega$	10	V/ns
P_D	$T_C = 25^\circ\text{C}$	700	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
V_{ISOL}	50/60 Hz; $I_{ISOL} \leq 1 \text{ mA}$	2500	V~
M_d	Mounting torque Terminal connection torque (M4)	1.5/13 Nm/ib.in. 1.5/13 Nm/ib.in.	
Weight		30	g

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 500 \mu\text{A}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 8 \text{ mA}$	3.0		5.0 V
I_{GSS}	$V_{GS} = \pm 30 \text{ V}_{DC}$, $V_{DS} = 0$			$\pm 200 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$			25 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 I_{D25}$, Note 1			65 m Ω

miniBLOC, SOT-227 B (IXFN)
E153432



G = Gate
S = Source
D = Drain

Either source tab S can be used for source current or Kelvin gate return.

Features

- Fast intrinsic diode
- International standard package
- Unclamped Inductive Switching (UIS) rated
- UL recognized.
- Isolated mounting base

Advantages

- Easy to mount
- Space savings
- High power density

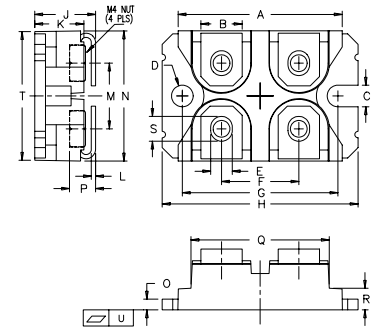
Symbol	Test Conditions	Characteristic Values (T _J = 25° C unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	V _{DS} = 20 V; I _D = 0.5 I _{D25} , Note 1	35	70	S
C_{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		12.7	nF
C_{oss}			1280	pF
C_{rss}			120	pF
t_{d(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 0.5*I _{D25} R _G = 2 Ω (External)		25	ns
t_r			27	ns
t_{d(off)}			70	ns
t_f			18	ns
Q_{g(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 0.5 I _{D25}		195	nC
Q_{gs}			70	nC
Q_{gd}			64	nC
R_{thJC}		0.05		0.18° C/W
R_{thCK}				° C/W

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values (T _J = 25° C unless otherwise specified)		
		Min.	Typ.	Max.
I_S	V _{GS} = 0 V			80 A
I_{SM}	Repetitive			200 A
V_{SD}	I _F = I _S , V _{GS} = 0 V, Note 1			1.5 V
t_{rr}	I _F = 25 A, -di/dt = 100 A/μs			200 ns
Q_{RM}	V _R = 100 V, V _{GS} = 0 V		0.8	μC
I_{RM}			8	A

Note 1: Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %

miniBLOC, SOT-227B (IXFN) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
one or more of the following U.S. patents:	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405B2	6,759,692
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2

Fig. 1. Output Characteristics
@ 25°C

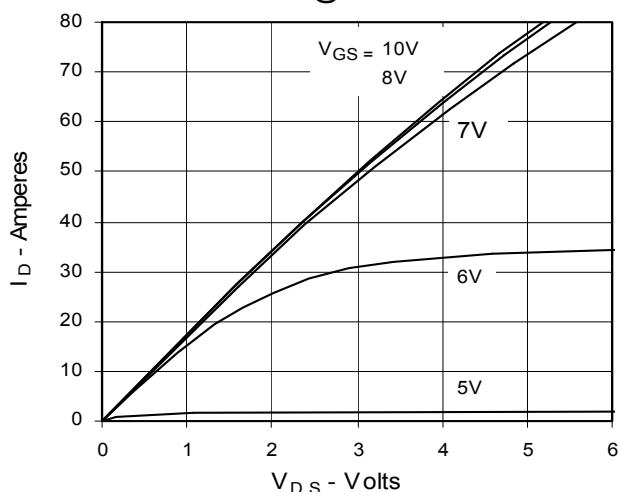


Fig. 2. Extended Output Characteristics
@ 25°C

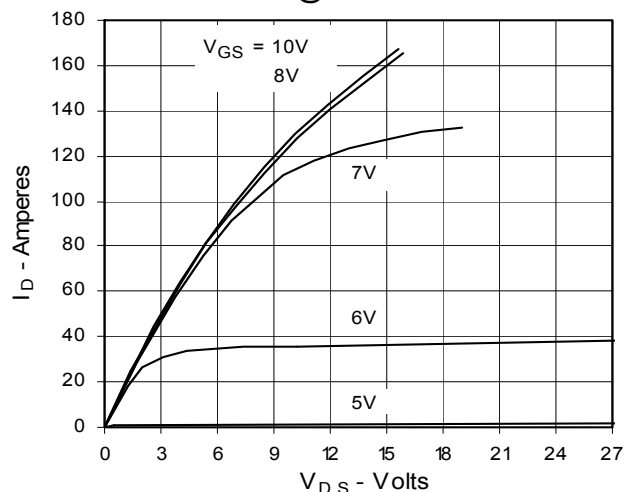


Fig. 3. Output Characteristics
@ 125°C

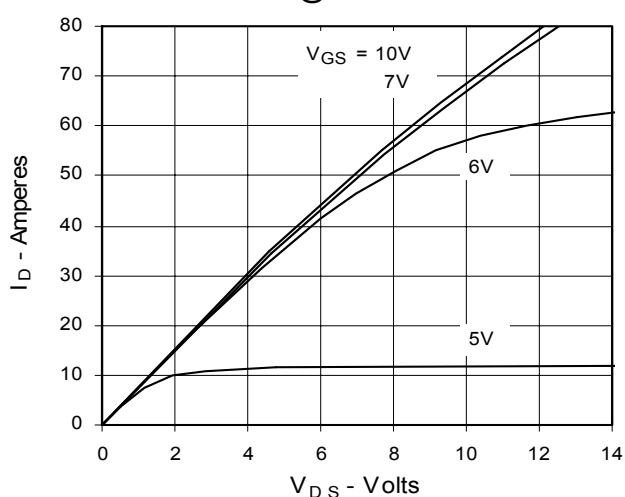


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 40A$
Value vs. Junction Temperature

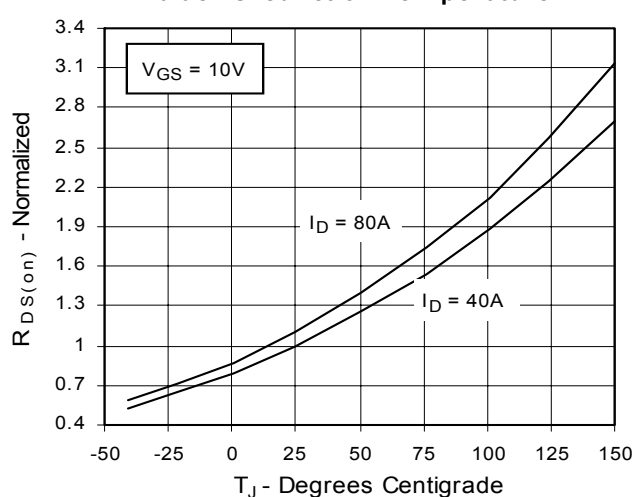


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 40A$
Value vs. Drain Current

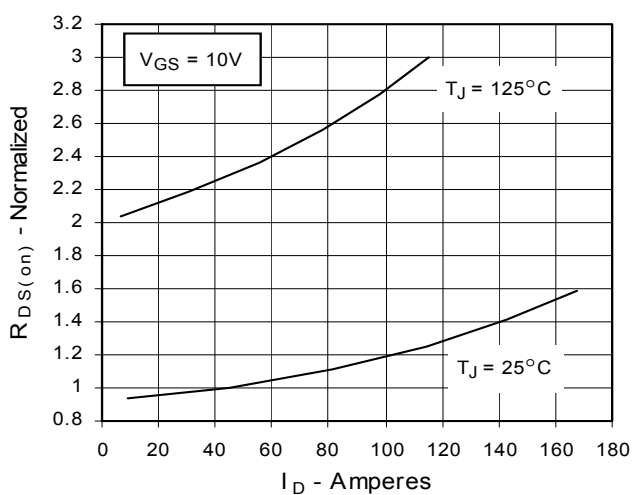


Fig. 6. Drain Current vs. Case Temperature

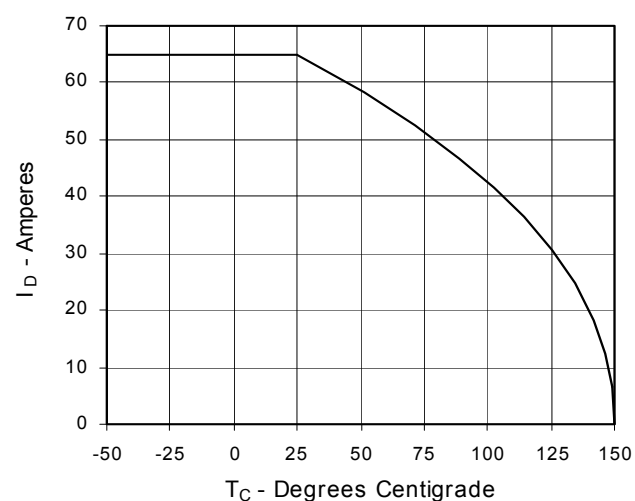


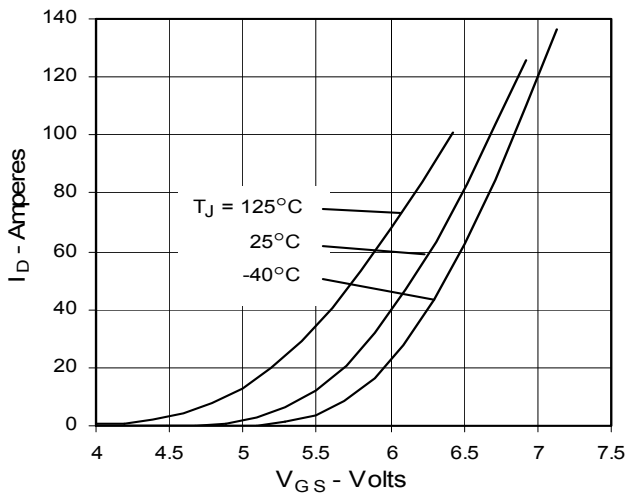
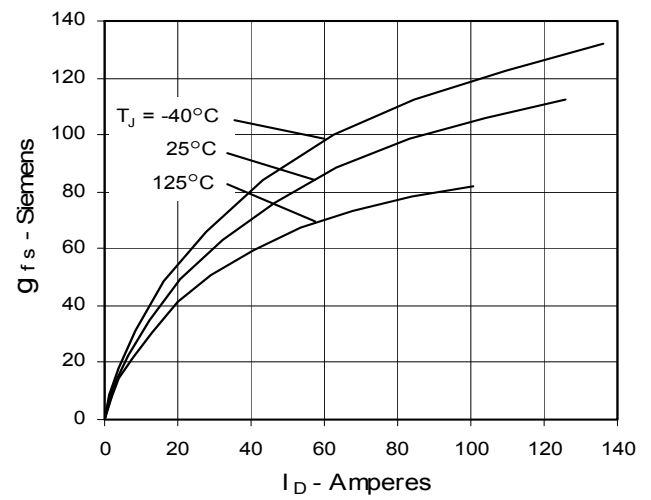
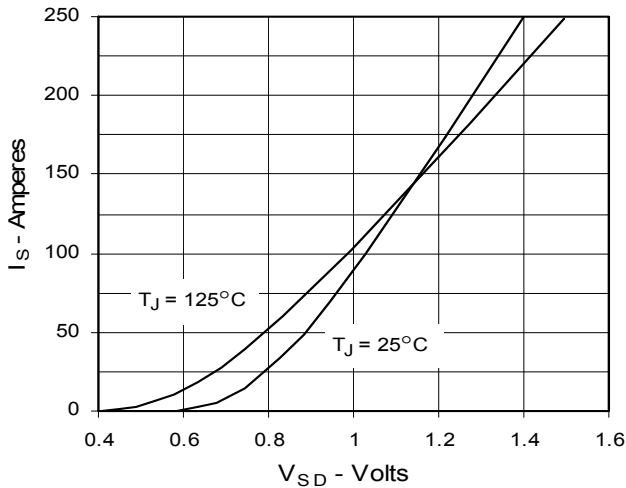
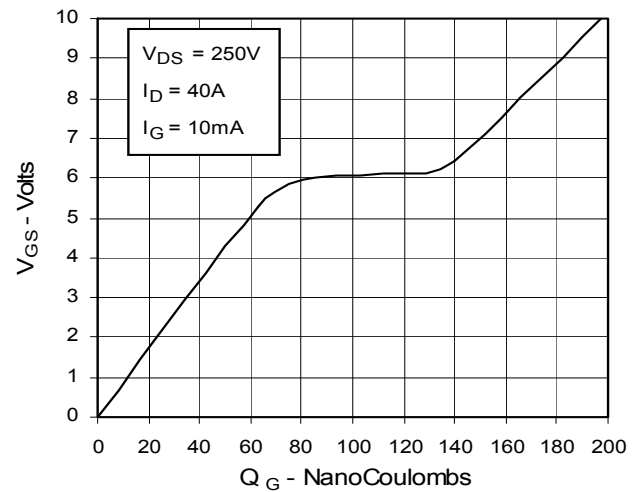
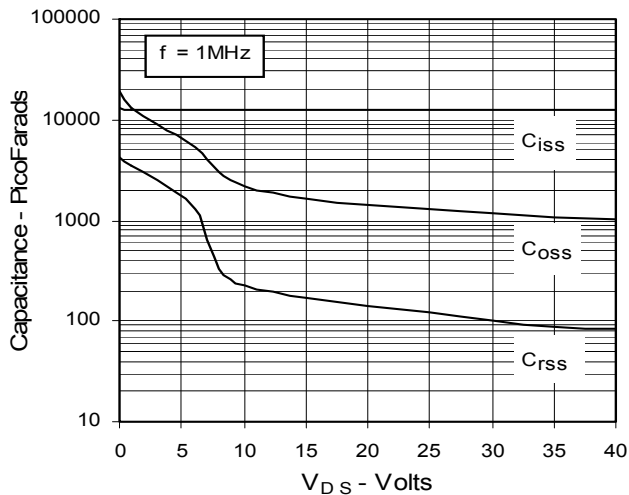
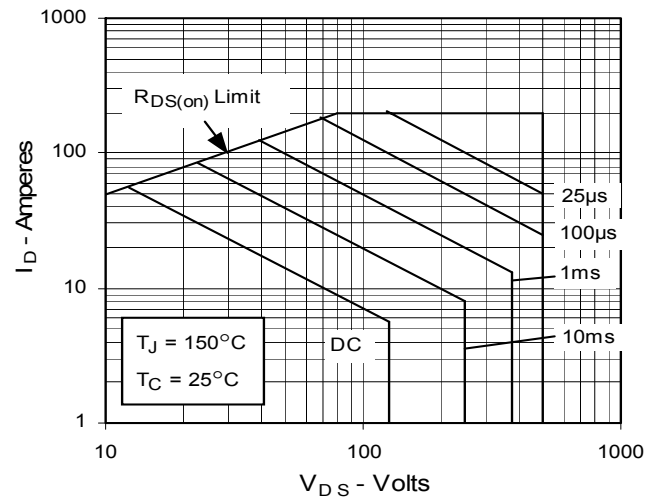
Fig. 7. Input Admittance

Fig. 8. Transconductance

Fig. 9. Source Current vs. Source-To-Drain Voltage

Fig. 10. Gate Charge

Fig. 11. Capacitance

Fig. 12. Forward-Bias Safe Operating Area


Fig. 13. Maximum Transient Thermal Resistance

